

SEMICONDUCTOR®

KSC839

FM/AM RADIO RF AMP, CONV, OSC, IF AMP

- Current Gain Bandwidth Product : f_T=200MHz
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



NPN Epitaxial Silicon Transistor

Abs	olute	Maximum	Ratings	T _a =25°C unless otherwise noted
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Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	35	V	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{EBO}	Emitter-Base Voltage	4	V	
I _C	Collector Current	100	mA	
P _C	Collector Power Dissipation	250	mW	
ТJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 ~ 150	°C	

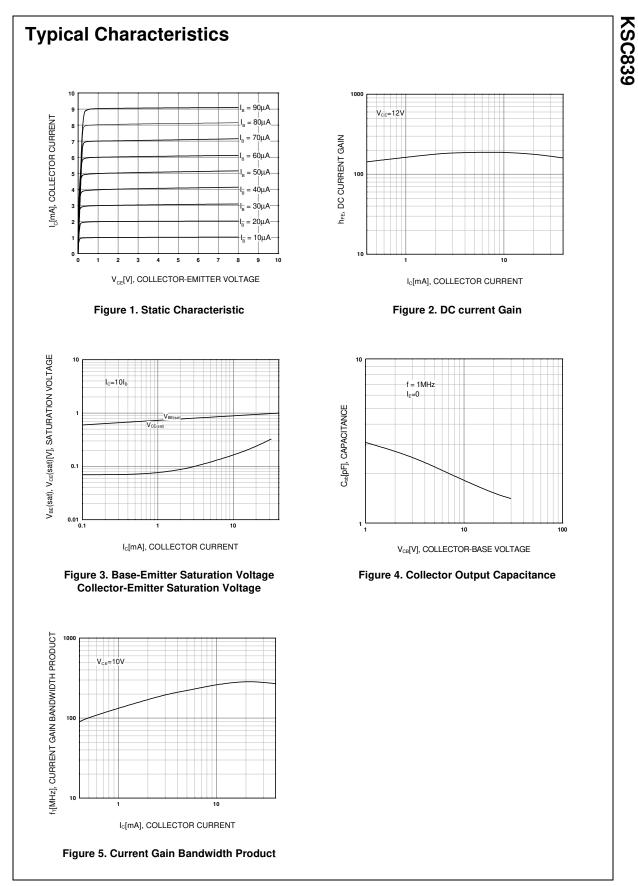
Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	35			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0	30			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	4			V
I _{CBO}	Collector Cut-off Current	V _{CB} =30V, I _E =0			0.1	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB}=4V, I_{C}=0$			0.1	μA
h _{FE}	DC Current Gain	V _{CE} =12V, I _C =2mA	40		400	
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =6V, I _C =1mA	0.65	0.70	0.75	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		0.1	0.4	V
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =1mA	80	200		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		2.0	3.5	pF

h_{FE} Classification

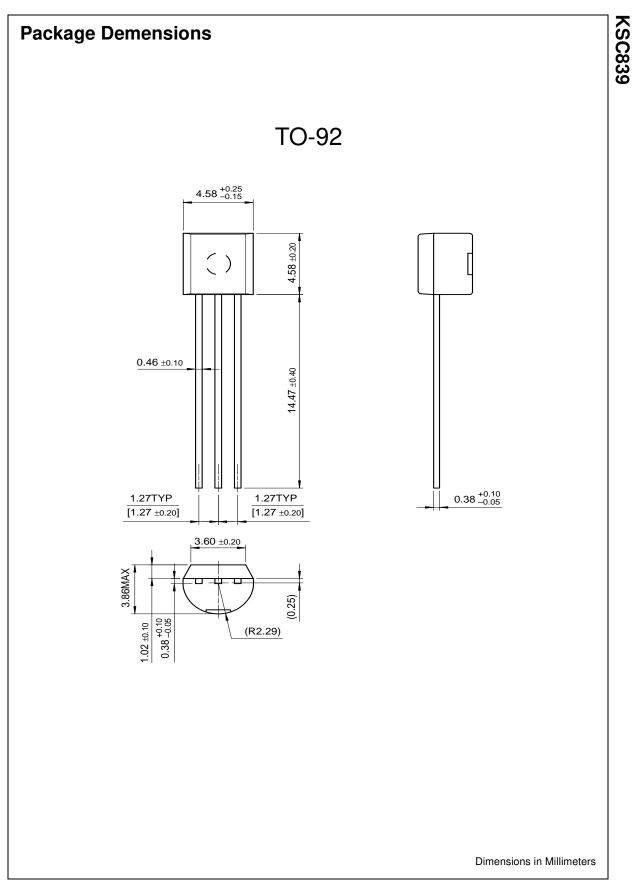
Classification	R	0	Y	G	
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	

KSC839



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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
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company

Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC839CYTA	Full Production	\$0.045	<u>TO-92</u>	3	TAPE REEL
KSC839YBU	Full Production	\$0.045	<u>TO-92</u>	3	BULK

* 1,000 piece Budgetary Pricing

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